

CERAMIC DISC CAPACITORS CHARACTERISTICS

項目 ITEM	規格 SPECIFICATION		檢測方法及條件 TEST METHOD AND CONDITION
10. 高溫負荷 (壽命試驗) Loading life High temperature Loading	外觀 Appearance	無顯著之異常。 No marked defect.	$\leq 500\text{VDC}$ 在試驗溫度下連續施加2倍W.V. (充放電電流50mA以下)1000(+48/-0)小時; $\geq 1\text{KVDC}$ 在試驗溫度下連續施加1.25倍W.V. (充放電電流50mA以下)1000(+48/-0)小時;
	靜電容量 變化率 Capacitance change	T.C.: $\pm 7.5\%$ or $\pm 0.75\text{PF}$;	$\leq 500\text{VDC}$ Apply 2 times rated voltage at maximum operating temperature for 1000(+48/-0)hours $\geq 1\text{KVDC}$ Apply 1.25 times rated voltage at maximum operating temperature for 1000(+48/-0)hours Test temp.: T.C., Y5E, Y5P, Y5U, Z5U, X5R Y5V, Z5V: $85^{\circ}\text{C} \pm 5^{\circ}\text{C}$ NPO N750, X7R: $125^{\circ}\text{C} \pm 5^{\circ}\text{C}$ Change or discharge current shall not exceed 50mA..
		HIK、半導體類(S.C.): Y5E、Y5P: $\pm 15\%$; X7R、X5R: $\pm 20\%$; Z5U、Y5U: $\pm 25\%$; Z5V、Y5V: $\pm 30\%$.	
	Q or DF	T.C. C<30PF: Q $\geq 200+10 \times C$ C $\geq 30\text{PF}$: Q ≥ 500	試驗后: 取出於室溫中, T.C.類需放置24小時以上方可測定; HIK、半導體類需放置48小時以上方可測定。 Capacitor shall be measured after leaving at room temperature T.C.:24Hr HIK, S.C.:48Hr
		HIK: Y5E、Y5P、X7R、 X5R、Z5U、Y5U Df $\leq 5\%$ Z5V、Y5V Df $\leq 7.5\%$	
半導體(S.C.): Y5P、Y5U Df $\leq 7.5\%$ Y5V Df $\leq 10\%$			
絕緣電阻 Insulation resistance	T.C.:1000M Ω min HIK:500M Ω min S.C.:25M $\Omega \times \text{UF}$ min		
11. 端子強度 Strength of lead	抗拉強度 Pull	導線不斷裂, 電容器本體不破損。 Lead wire shall not cut off and capacitor shall not be broken.	垂直固定被測物本體, 引線向下, 負荷施力方向為端線引出方向, 施加負荷為1.0kg,時間為5秒 As a figure fix the body of capacitor, apply a tensile weight gradually to each lead in the radial direction of capacitor up to 1.0kg, and keep it for 5 secretary..
	彎曲強度 Bending		固定被測物, 施加0.5kg於端子引線間並彎曲90°, 回復原來之位置, 並反向彎曲90°, 1次彎曲時間為5秒。 Each lead wire shall be subjected to 0.5kg weight and then a 90° bend, at the point of egress, in one direction, return to original position and then a 90° bend in the opposite direction at the rate of one bend in 5 secretary..